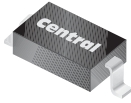


CMDD2004

**SURFACE MOUNT  
HIGH VOLTAGE SILICON  
SWITCHING DIODE**

**SUPERmini™**



**SOD-323 CASE**



[www.centrasemi.com](http://www.centrasemi.com)

**DESCRIPTION:**

The Central Semiconductor CMDD2004 is a high voltage silicon switching diode manufactured by the epitaxial planar process, epoxy molded in a SUPERmini™ surface mount package, designed for applications requiring high voltage capability.

**MARKING CODE: C24**

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

Continuous Reverse Voltage  
Peak Repetitive Reverse Voltage  
Peak Repetitive Reverse Current  
Continuous Forward Current  
Peak Repetitive Forward Current  
Peak Forward Surge Current,  $t_p=1.0\mu\text{s}$   
Peak Forward Surge Current,  $t_p=1.0\text{s}$   
Power Dissipation  
Operating and Storage Junction Temperature  
Thermal Resistance

**SYMBOL**

$V_R$  240  
 $V_{RRM}$  300  
 $I_O$  200  
 $I_F$  225  
 $I_{FRM}$  625  
 $I_{FSM}$  4.0  
 $I_{FSM}$  1.0  
 $P_D$  250  
 $T_J, T_{stg}$  -65 to +175  
 $\theta_{JA}$  600

**UNITS**

V  
V  
mA  
mA  
mA  
A  
A  
mW  
 $^\circ\text{C}$   
 $^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

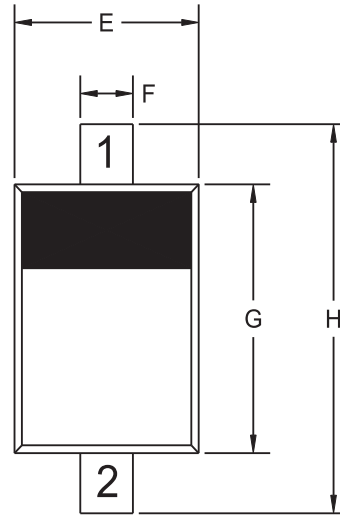
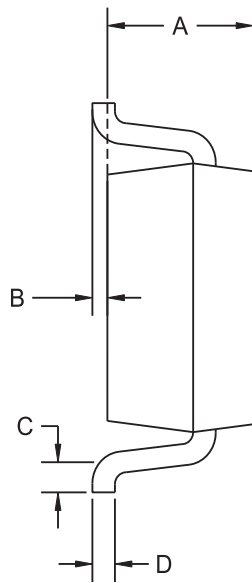
SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
$I_R$	$V_R=240\text{V}$		100	nA
$I_R$	$V_R=240\text{V}, T_A=150^\circ\text{C}$		100	$\mu\text{A}$
$BV_R$	$I_R=100\mu\text{A}$	300		V
$V_F$	$I_F=100\text{mA}$		1.0	V
$C_T$	$V_R=0, f=1.0\text{MHz}$		5.0	pF
$t_{rr}$	$I_F=I_R=30\text{mA}, \text{Rec. to } 3.0\text{mA}, R_L=100\Omega$		50	ns

CMDD2004

SURFACE MOUNT  
HIGH VOLTAGE SILICON  
SWITCHING DIODE



SOD-323 CASE - MECHANICAL OUTLINE



R4

LEAD CODE:

- 1) CATHODE
- 2) ANODE

MARKING CODE: C24

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.031	0.039	0.80	1.00
B	0.000	0.004	0.00	0.10
C	0.008	-	0.20	-
D	0.004	0.007	0.11	0.19
E	0.045	0.053	1.15	1.35
F	-	0.014	-	0.35
G	0.063	0.071	1.60	1.80
H	0.094	0.102	2.40	2.60

SOD-323 (REV: R4)

R5 (8-January 2010)